



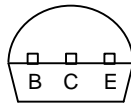
Shanghai Lunsure Electronic
Technology Co.,Ltd
Tel:0086-21-37185008
Fax:0086-21-57152769

2SC945

Features

- Capable of 0.4Watts of Power Dissipation.
- Collector-current 0.15A
- Collector-base Voltage 60V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration
Bottom View



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage ($I_C=0.1mA_{dc}, I_B=0$)	50		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=1000\mu A_{dc}, I_E=0$)	60		Vdc
$V_{(BR)EBO}$	Emmitter-Base Breakdown Voltage ($I_E=100\mu A_{dc}, I_C=0$)	5.0		Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=60V_{dc}, I_E=0A_{dc}$)		0.1	μA_{dc}
I_{CER}	Collector Cutoff Current ($V_{CE}=55V_{dc}, R=10M\ OHM$)		0.1	μA_{dc}
I_{EBO}	Emmitter Cutoff Current ($V_{EB}=5.0V_{dc}, I_C=0A_{dc}$)		0.1	μA_{dc}

ON CHARACTERISTICS

$h_{FE(1)}$	DC Current Gain ($I_C=1.0mA_{dc}, V_{CE}=6.0V_{dc}$)	70	700	
$h_{FE(2)}$	DC Current Gain ($I_C=0.1mA_{dc}, V_{CE}=6.0V_{dc}$)	40		
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage ($I_C=100mA_{dc}, I_B=10mA_{dc}$)		0.3	Vdc
$V_{BE(sat)}$	Base-Emmitter Saturation Voltage ($I_C=100mA_{dc}, I_B=10mA_{dc}$)		1.0	Vdc
V_{BE}	Base-Emmitter Voltage ($I_E=310mA_{dc}$)		1.4	Vdc

SMALL-SIGNAL CHARACTERISTICS

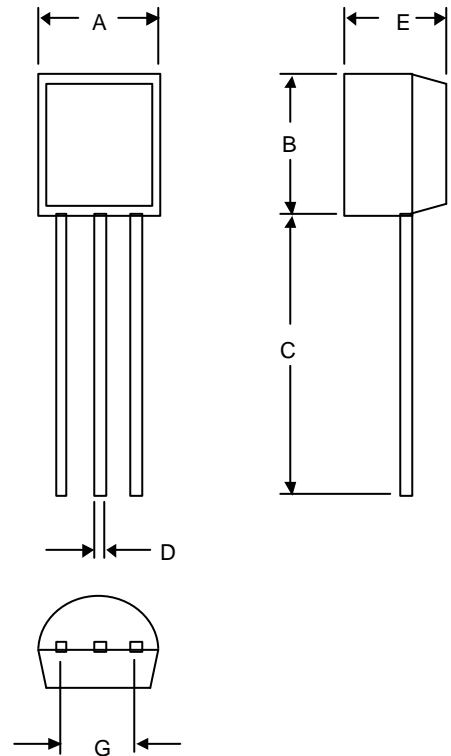
f_T	Transistor Frequency ($I_C=10mA_{dc}, V_{CE}=6.0V_{dc}, f=30MHz$)	150		MHz
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CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

NPN Silicon Plastic-Encapsulate Transistor

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	